

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:	)	
	:	Examiner: George R. Fourson, III
Kiyofumi SAKAGUCHI, et al.	)	
	:	Group Art Unit: 2823
Application No.: 09/161,774	)	
	:	Confirmation No.: 8032
Filed: September 29, 1998	)	
	:	
For: PROCESS FOR PRODUCTION OF	)	September 8, 2006
SEMICONDUCTOR SUBSTRATE	:	

**Mail Stop Amendment**  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

SIXTH INFORMATION DISCLOSURE STATEMENT

Sir:

In compliance with the duty of disclosure under 37 C.F.R. § 1.56 and in accordance with the practice under 37 C.F.R. §§ 1.97 and 1.98, the Examiner's attention is directed to the documents listed on the enclosed Form PTO-1449. Copies of the listed documents, other than U.S. patent documents, are enclosed.

REMARKS

An English-language Abstract for JP-A 60-196955 was obtained from a commercial database and is also enclosed.

### FORMAL MATTERS

No fee is believed due; however, any fee required in connection with this paper should be charged to Deposit Account No. 06-1205.

### CONCLUSION

It is respectfully requested that the above information be considered by the Examiner and that a copy of the enclosed Form PTO-1449 be returned indicating that such information has been considered.

Applicant's undersigned attorney may be reached in our Washington, D.C. office by telephone at (202) 530-1010. All correspondence should continue to be directed to our address given below.

Respectfully submitted,

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FORM PTO 1449 (modified)  U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE  LIST OF REFERENCES CITED BY APPLICANT(S) (Use several sheets if necessary)  <b>Dated Submitted to USPTO: September 8, 2006</b>				ATTY DOCKET NO. <b>03500.010530.4</b> (35.C10530 C1/D2)		APPLICATION NO. <b>09/161,774</b>	
				APPLICANT <b>Kiyofumi SAKAGUCHI, et al.</b>			
				FILING DATE <b>September 29, 1998</b>		GROUP <b>2823</b>	
U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		<b>5,175,610</b>	<b>12/29/1992</b>	<b>Kobayashi</b>	<b>257</b>	<b>676</b>	
		<b>4,670,763</b>	<b>06/02/1987</b>	<b>Ovshinsky, et al.</b>	<b>357</b>	<b>4</b>	
		<b>4,555,586</b>	<b>11/26/1985</b>	<b>Guha, et al.</b>	<b>136</b>	<b>259</b>	
		<b>4,426,657</b>	<b>01/17/1984</b>	<b>Abiru, et al.</b>	<b>357</b>	<b>29</b>	
		<b>4,064,521</b>	<b>12/20/1977</b>	<b>Carlson</b>	<b>357</b>	<b>2</b>	
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO/ OR ABSTRACT
		<b>60-196955</b>	<b>10/05/1985</b>	<b>Japan</b>			<b>Abstract</b>
		<b>0 469 630 A2</b>	<b>02/05/1992</b>	<b>Europe</b>			
OTHER DOCUMENT(S) (Including Author, Title, Date, Pertinent Pages, Etc.)							
		<b>T. Yasumatsu, et al., "Ultrathin Si Films Grown Epitaxially on Porous Silicon", Applied Surface Science, Vols. 48 &amp; 49, pp. 414-418 (1991)</b>					
		<b>Handbook of Thin Film Technology, 5-17 to 5-25 (Eds., L. I. Maissel and R. Glang 1970)</b>					
		<b>Robert F. Pierret, <u>Semiconductor Device Fundamentals</u>, pp. 347-368</b>					
EXAMINER				DATE CONSIDERED			

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO/ OR ABSTRACT
OTHER DOCUMENT(S) (Including Author, Title, Date, Pertinent Pages, Etc.)							
		<b>S.M. Sze, Physics of Semiconductor Devices, pp. 63-128, 847-849, 2<sup>nd</sup> Edition (1981)</b>					
		<b>W. Kern &amp; V. Ban, <u>Thin Film Processes</u>, Chemical Vapor Deposition of Inorganic Thin Films, pp. 257-331 (1978)</b>					
		<b>W. Luft &amp; Y. Tsuo, <u>Hydrogenated Amorphous Silicon Alloy Deposition Processes</u>, pp. 125-144 (1993)</b>					
		<b>R. Pierret, Modular Series on Solid State Devices, Vol. 4, pp. 59-80 (1983)</b>					
EXAMINER				DATE CONSIDERED			

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